MMIC Amplifier, 3 V, 16 mA, 0.1 to 3.6 GHz, MCPH6

NSVG3109SG6

Features

- High Gain: Gp = 23 dB typ. @ 1 GHz
- Wideband response: fu = 3.6 GHz
- Low current: $I_{CC} = 16 \text{ mA typ.}$
- High output power: Po (1dB) = 4 dBm
- Port impedance: input/output: 50 Ω
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- This is a Pb–Free Device

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Symbol	Parameter Ratings U		
V _{CC}	Supply Voltage	5	V
I _{CC}	Circuit Current	25	mA
PD	Allowable Power Dissipation	280	mW
Topr	Operating Temperature	– 40 to +85	°C
Tstg	Storage Temperature - 55 to +150		°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS (Ta = 25°C)

		Ratings			
Symbol	Parameter	Min	Тур	Max	Unit
V _{CC}	Supply Voltage	2.7	3	3.3	V
Topr	Operating Ambient Temperature	- 40	+25	+85	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.



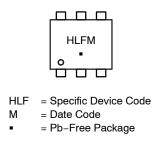
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SC88FL / MCPH6 CASE 419AS

MARKING DIAGRAM



ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

NSVG3109SG6

	Parameter	Conditions		Ratings		
Symbol			Min	Тур	Max	Unit
I _{CC}	Circuit Current		11.5	16.0	20.5	mA
Gp	Power Gain	f = 1 GHz	21.0	23.0	26.0	dB
		f = 2.2 GHz	22.0	24.0	27.0	
ISL	Isolation	f = 1 GHz	27.0	31.5	-	dB
		f = 2.2 GHz	27.0	31.5	-	
RLin	Input Return Loss	f = 1 GHz	16.0	20.5	-	dB
		f = 2.2 GHz	10.0	15.0	-	
RLout	Output Return Loss	f = 1 GHz	15.0	20.0	-	dB
		f = 2.2 GHz	10.0	14.0	-	
NF	Noise Figure	f = 1 GHz	-	4.3	5.0	dB
		f = 2.2 GHz	-	4.3	5.0	
Po (1dB)	Gain 1dB Compression Output Power	f = 1 GHz	4.0	6.4	-	dBm
		f = 2.2 GHz	2.0	4.2	-	
fu	Upper Limit Operating Frequency	3 dB down below flat gain at f = 1GHz	-	3.6	-	GHz

ELECTRICAL CHARACTERISTICS (Ta = 25°C, V_{CC} = 3 V, Zs = Z_L = 50 Ω)

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 1. Pay attention to handling since it is liable to be affected by static electricity due to the high frequency process adopted.

Test Circuit

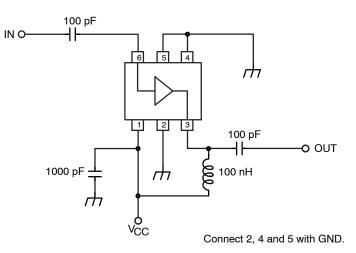
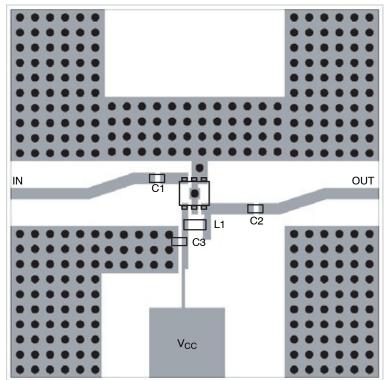


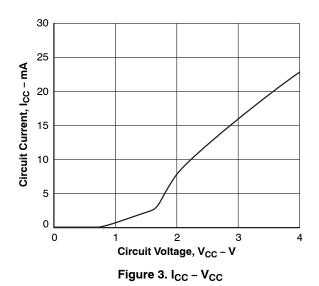
Figure 1. Test Circuit



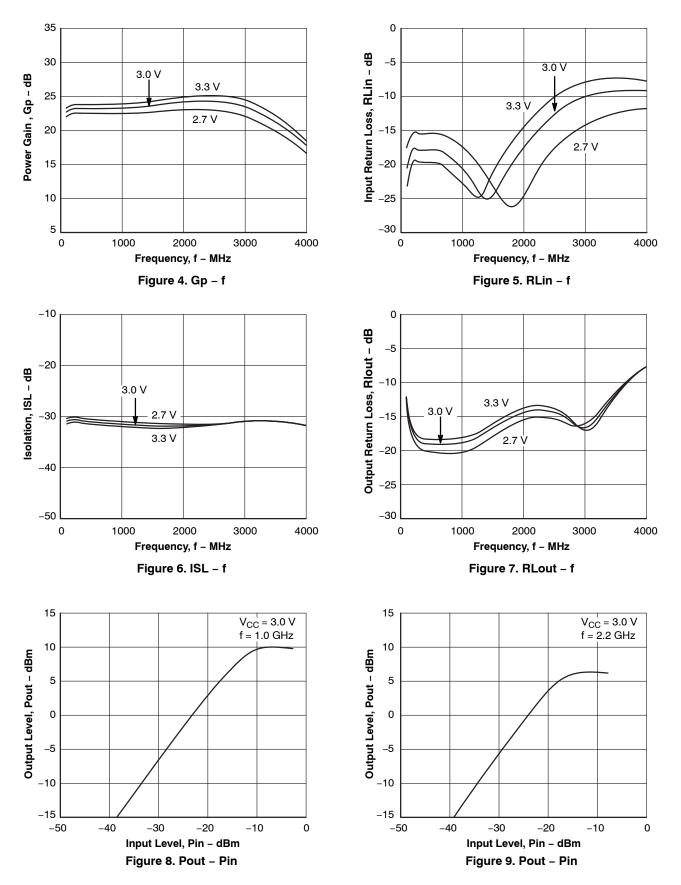
Symbol	Value
C1, C2	100 pF
C3	1000 pF
L1	100 nH

Figure 2. Evaluation Board

Characteristics

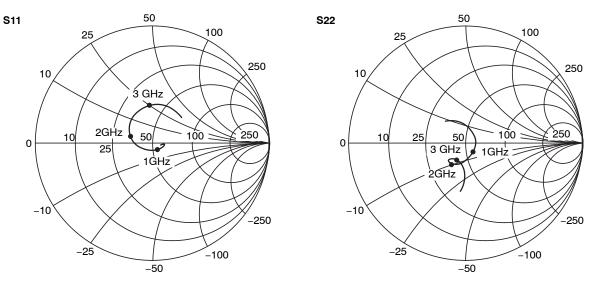


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S Parameter



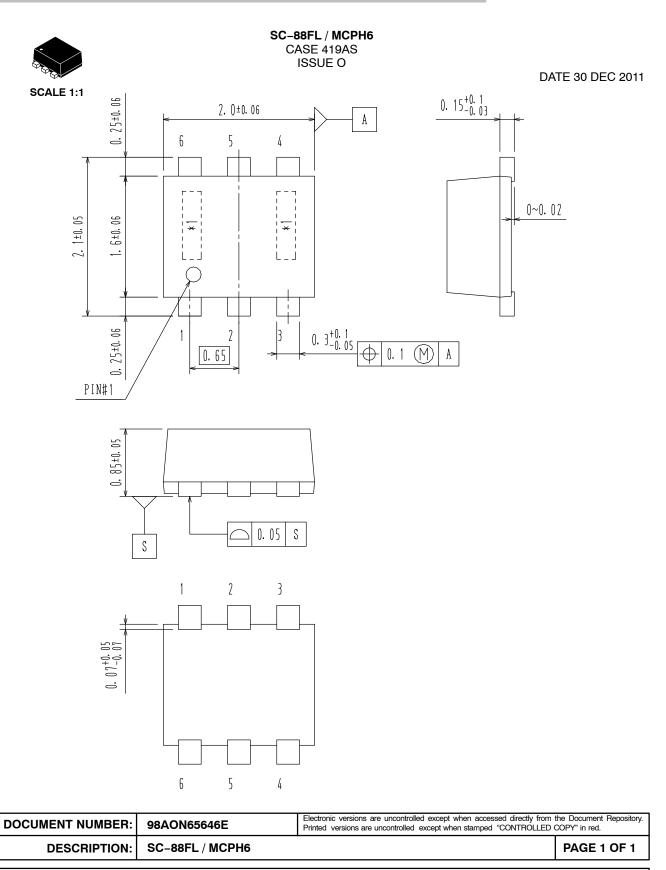


ORDERING INFORMATION

Device Order Number	Specific Device Marking	Package Type (JEITA, JEDEC)	Package Type	Shipping [†]
NSVG3109SG6T1G	HLF	SC82, SC82A, SC88 (Pb–Free)	MCPH6 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.





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